





Linear Systems replaces discontinued Siliconix PAD1

The PAD1 is a low leakage Pico-Amp Diode packaged in hermetic TO-72

The PAD1 extremely low-leakage diode provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. The PAD1 features a leakage current of -1 pA and is well suited for use in applications such as input protection for operational amplifiers.

PAD1 Benefits:

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes
- Simplicity of Operation

PAD1 Applications:

- Op Amp Input Protection
- Multiplexer Overvoltage Protection

FEATURES							
DIRECT REPLACEMENT FOR SILICONIX PAD1							
REVERSE BREAKDOWN VOLTAGE	BV _R ≥ -45V						
ULTRALOW LEAKAGE	≤ 1 pA						
REVERSE CAPACITANCE	C _{rss} ≤ 0.8pF						
ABSOLUTE MAXIMUM RATINGS							
@ 25°C (unless otherwise noted)							
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Maximum Temperatures							
Storage Temperature	-65°C to +150°C						
Operating Junction Temperature	-55°C to +135°C						
Maximum Power Dissipation							
ontinuous Power Dissipation 300mW							
MAXIMUM CURRENT							
Forward Current (Note 1)	50mA						

PAD1 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV _R	Reverse <mark>Br</mark> ea <mark>kdo</mark> wn Voltage	-4 5-		-	V	1μA
V _F	Forward Voltage		0.8	1.5	V	$I_F = 5mA$
C _{rSS}	Total Reverse Capacitance		0.5	0.8	pF	$V_R = -5V$, $f = 1MHz$
I _R	Maximum Reverse Leakage Current			-1	pA	V _R = - 20V

Notes:

1. Absolute maximum ratings are limiting values above which PAD1 serviceability may be impaired.

Available Packages:

PAD1 in TO-72

PAD1 available as bare die

Please contact Micross for full package and die dimensions



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